

Radiation	Type	Technology	Case
Infrared	DH	AlGaAs/GaAs	5 mm plastic lens

		Description
		High-power NIR-LED, housing without standoff leads Note: Special packages with standoff available on request
Applications		Remote control, safety equipment, automation

Maximum Ratings

$T_{amb} = 25^\circ C$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I_F	100	mA
Peak forward current	($t_P \leq 50 \mu s$, $t_P/T = 1/2$)	I_{FM}	200	mA
Reverse voltage	$I_R = 10 \mu A$	V_R	5	V
Power dissipation		P_D	280	mW
Operating temperature range		T_{amb}	-20 to +100	°C
Storage temperature range		T_{stg}	-55 to +100	°C
Junction temperature		T_J	100	°C

Optical and Electrical Characteristics

$T_{amb} = 25^\circ C$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	V_F		1,4	1,6	V
Radiant power	$I_F = 100 \text{ mA}$	Φ_e	20	30		mW
Radiant intensity	$I_F = 100 \text{ mA}$	I_e	50	70		mW/sr
Peak wavelength	$I_F = 100 \text{ mA}$	λ_P	920	935	950	nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		50		nm
Viewing angle	$I_F = 100 \text{ mA}$	φ		25		deg.
Switching time	$I_F = 100 \text{ mA}$	t_r, t_f		600		ns

Note: All measurements carried out on *EPIGAP* equipment

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.